

1.Description

The AO4468 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

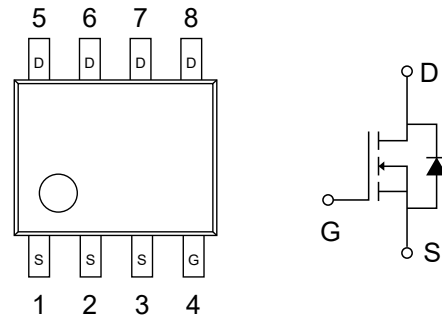
2.Features

- $V_{DS(V)}=30V$
- $I_D=10.5A$
- $R_{DS(ON)}<17m\Omega(V_{GS}=10V)$
- $R_{DS(ON)}<23m\Omega(V_{GS}=4.5V)$

3.Pinning information

Pin	Symbol	Description
4	G	GATE
1,2,3	S	SOURCE
5,6,7,8	D	DRAIN

SOP-8



4.Absolute Maximum Ratings $T_A=25^{\circ}C$

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A=25^{\circ}C$	I_D	10.5	A
	$T_A=70^{\circ}C$		8.5	
Pulsed Drain Current [°]		I_{DM}	50	
Avalanche Current [°]		I_{AS}, I_{AR}	19	
Avalanche energy $L=0.1mH$ [°]		E_{AS}, E_{AR}	18	mJ
Power Dissipation ^B	$T_A=25^{\circ}C$	P_D	3.1	W
	$T_A=70^{\circ}C$		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}C$



5.Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	31	40	°C/W
Maximum Junction-to-Ambient ^{AD}	Steady-State		59	75	°C/W
Maximum Junction-to-Lead	Steady-State	R _{θJL}	16	24	°C/W



6. Electrical Characteristic ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$T_J=55^{\circ}\text{C}$			5	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 16\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.2	1.8	2.4	V
On state drain current	$I_{D(ON)}$	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	50			A
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=10.5\text{A}$		14	17	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=9\text{A}$		18	23	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=5\text{V}$, $I_D=10.5\text{A}$		36		S
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.75	1	V
Maximum Body-Diode Continuous Current	I_S				4	A
DYNAMIC PARAMETERS						
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		740	888	pF
Output Capacitance	C_{oss}			110	145	pF
Reverse Transfer Capacitance	C_{rss}			82	115	pF
Gate resistance	R_g	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$	0.5	1.1	1.7	Ω
SWITCHING PARAMETERS						
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$ $I_D=10.5\text{A}$		15		nC
Total Gate Charge	$Q_g(4.5\text{V})$			7.5		nC
Gate Source Charge	Q_{gs}			2.5		nC
Gate Drain Charge	Q_{gd}			3		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$ $R_L=1.45\Omega$, $R_{GEN}=3\Omega$		5		ns
Turn-On Rise Time	t_r			3.5		ns
Turn-Off DelayTime	$t_{D(off)}$			19		ns
Turn-Off Fall Time	t_f			3.5		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F=10.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		18	22	ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=10.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		9	12	nC



- A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.
- C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
- D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.



7.1 Typical characteristic

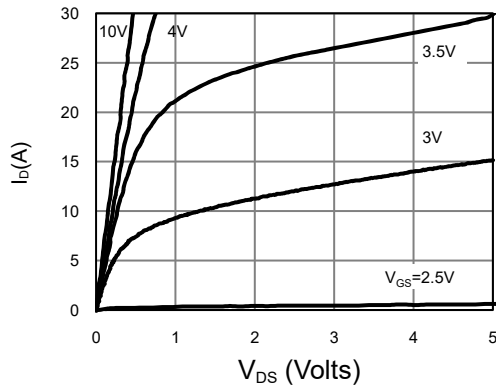


Fig 1: On-Region Characteristics

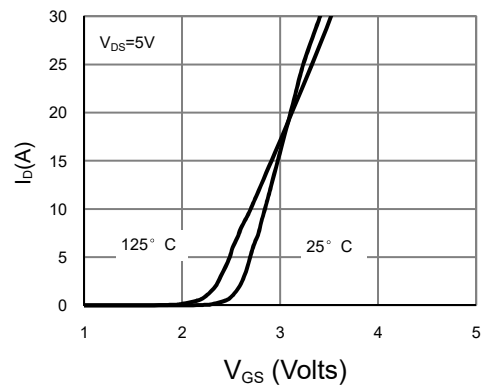


Figure 2: Transfer Characteristics (Note E)

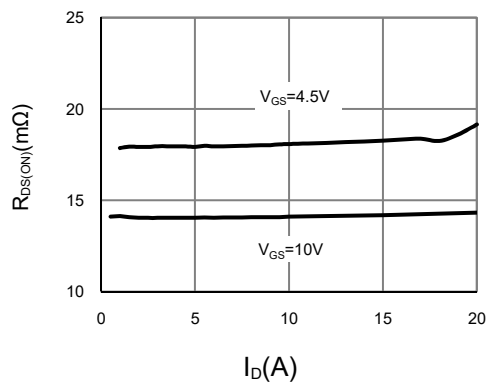


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

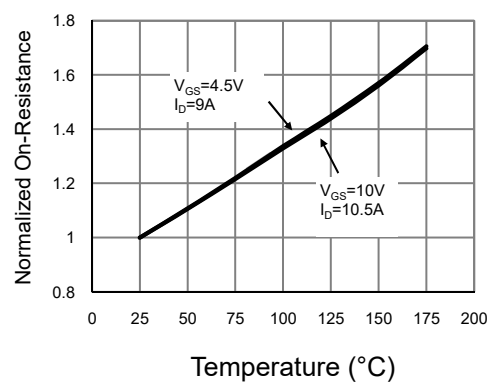


Figure 4: On-Resistance vs. Junction Temperature (Note E)

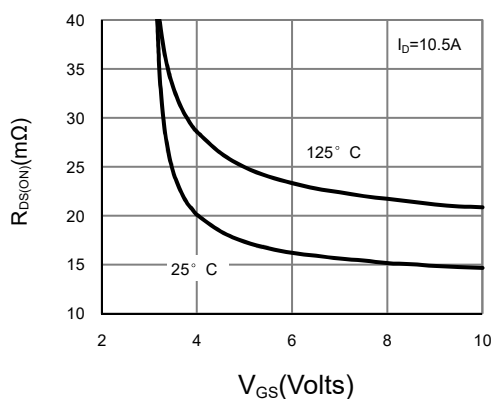


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

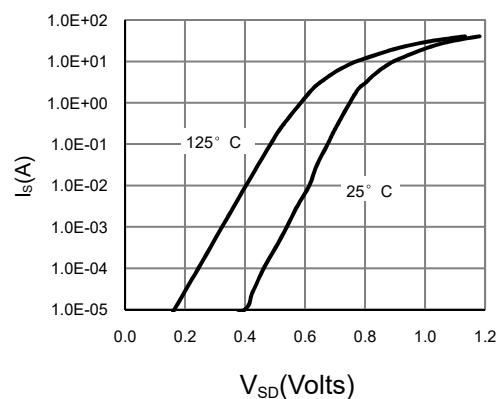


Figure 6: Body-Diode Characteristics (Note E)



7.2 Typical characteristic

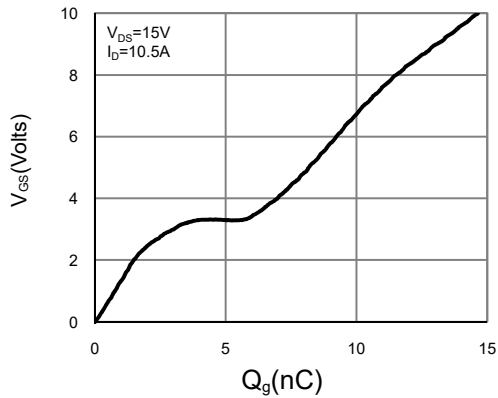


Figure 7: Gate-Charge Characteristics

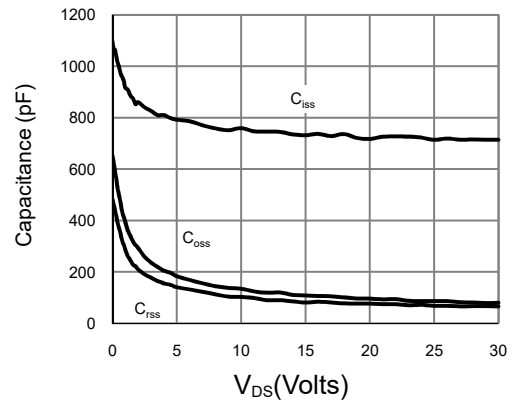


Figure 8: Capacitance Characteristics

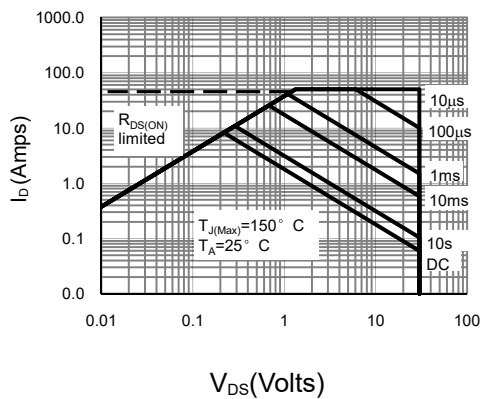


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

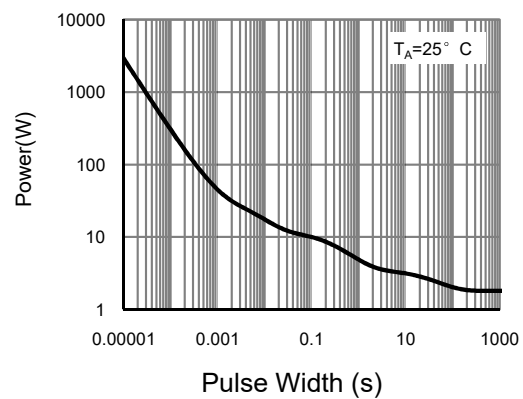


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

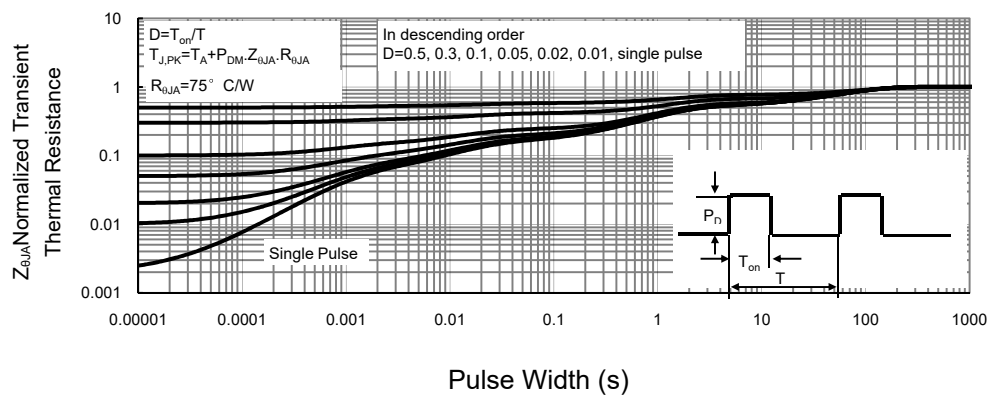
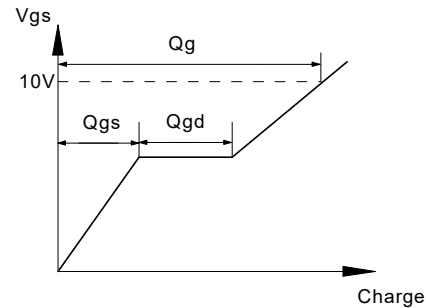
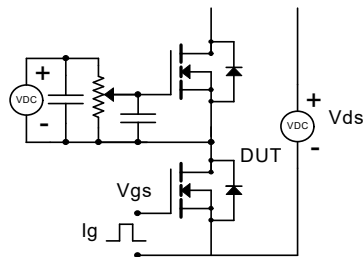


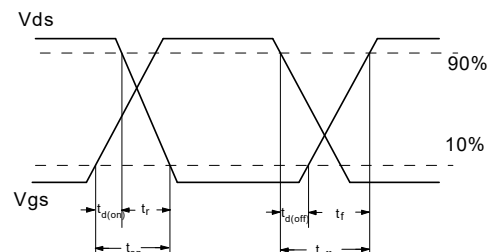
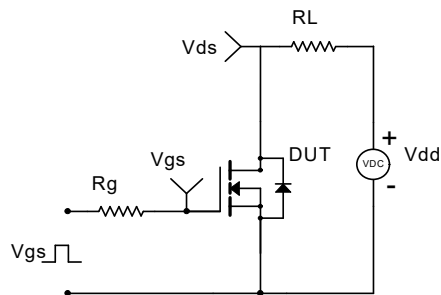
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)



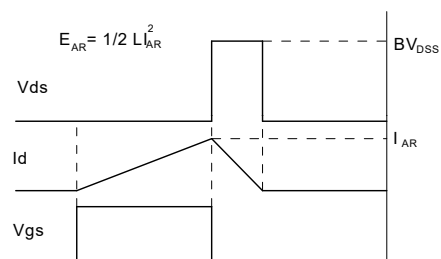
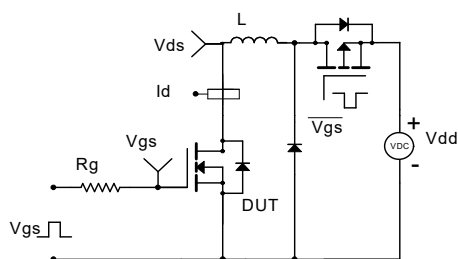
Gate Charge Test Circuit & Waveform



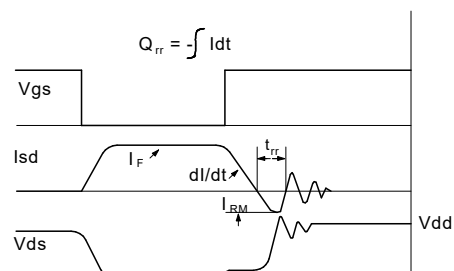
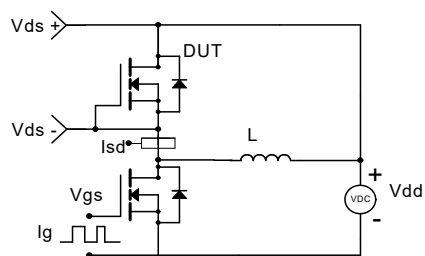
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

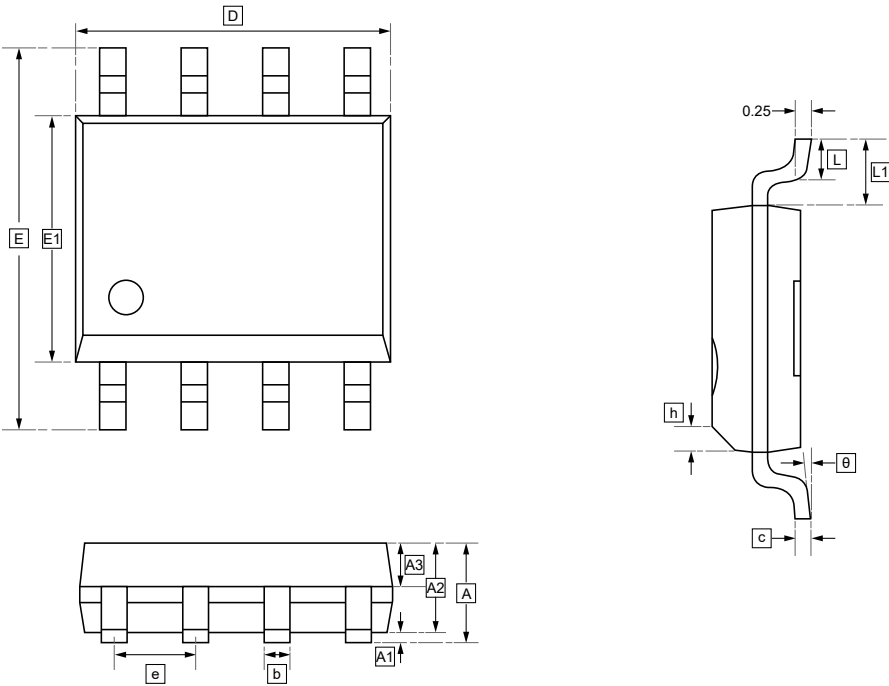


Diode Recovery Test Circuit & Waveforms





8.SOP-8 Package Outline Dimensions



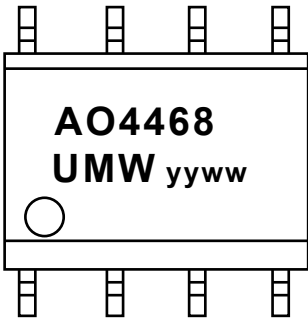
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	b	c	D	E	E1	e	h	L
Min	-	0.05	1.30	0.60	0.39	0.20	4.80	5.80	3.80	1.24	0.30	0.50
Max	1.75	0.20	1.50	0.70	0.47	0.24	5.00	6.20	4.00	1.30	0.50	0.80

Symbol	L1	θ
Min	1.00	0°
Max	1.10	8°



9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW AO4468	SOP-8	3000	Tape and reel



10.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

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